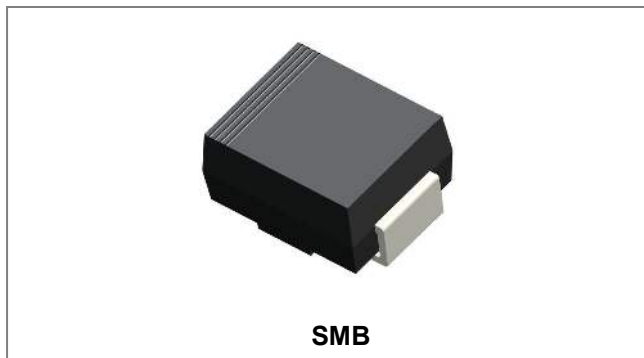


## 10BQ100 SCHOTTKY RECTIFIER



### Features

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	100	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 152^\circ\text{C}$ , rectangular wave form	1.0	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse, $T_C = 25^\circ\text{C}$	45	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 1 A, Pulse, $T_J = 25^\circ\text{C}$ @ 2 A, Pulse, $T_J = 25^\circ\text{C}$	0.76 -	0.78 0.89	V
	$V_{F2}$	@ 1 A, Pulse, $T_J = 125^\circ\text{C}$ @ 2 A, Pulse, $T_J = 125^\circ\text{C}$	0.60 -	0.62 0.72	V
Reverse Current*	$I_{R1}$	@ $V_R = \text{Rated } V_R$ , Pulse, $T_J = 25^\circ\text{C}$	0.00002	0.5	mA
	$I_{R2}$	@ $V_R = \text{Rated } V_R$ , Pulse, $T_J = 125^\circ\text{C}$	0.02	1	mA
Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	26	42	pF
Series Inductance	$L_S$	Measured lead to lead 5 mm from package body	2.0	-	nH
Voltage Rate of Change	$dv/dt$	-	-	10,000	V/ $\mu\text{s}$

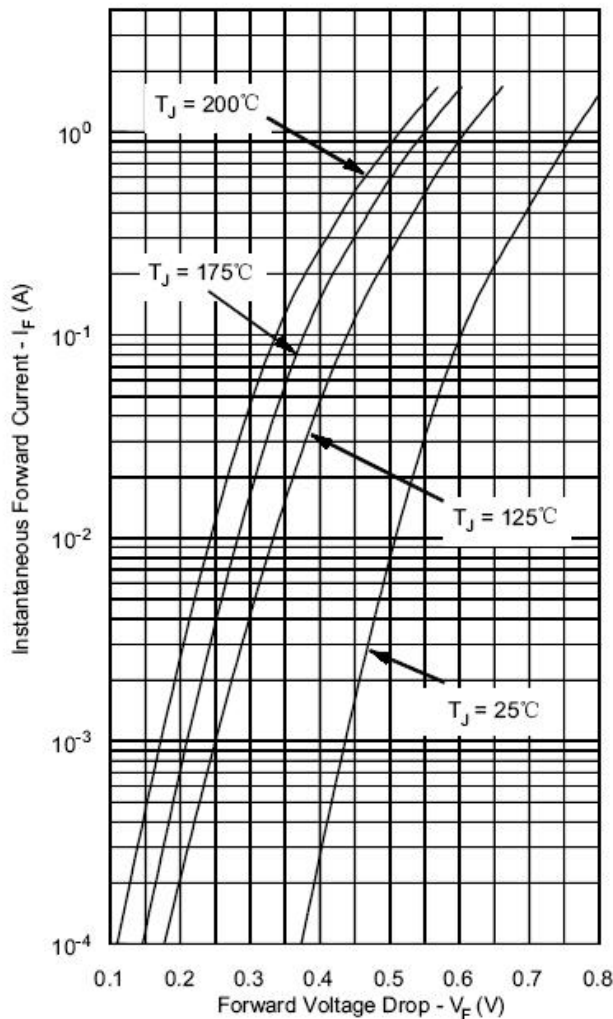
\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

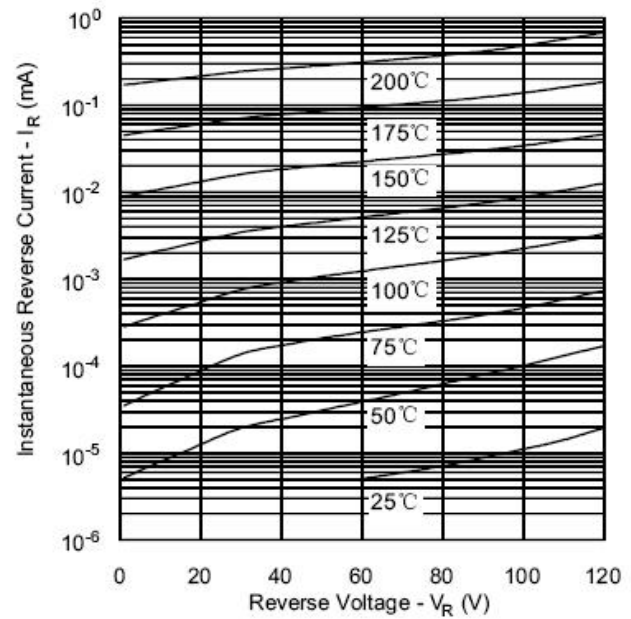
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +175	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +175	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Lead	$R_{\theta\text{JL}}$	-	36	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	0.09	g
Case Style		SMB		

**Ratings and Characteristics Curves**

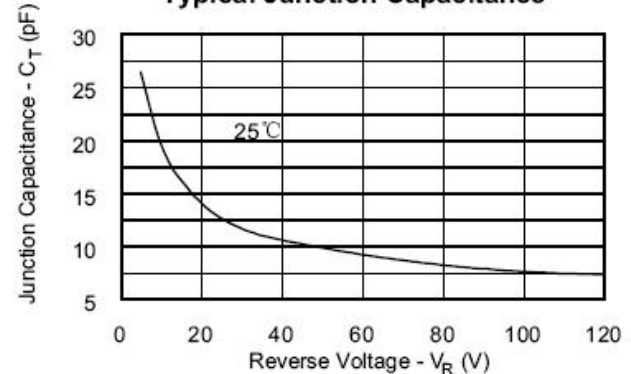
**Typical Forward Characteristics**



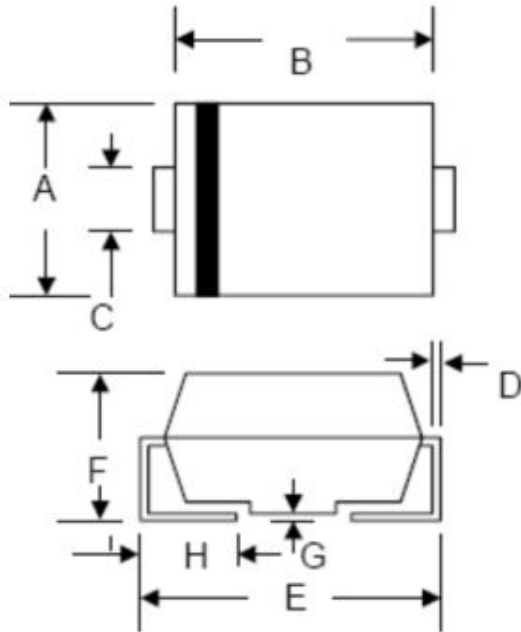
**Typical Reverse Characteristics**



**Typical Junction Capacitance**



**Mechanical Dimensions SMB**



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.80	2.20	0.071	0.087
D	0.152	0.305	0.006	0.012
E	4.80	5.59	0.189	0.220
F	2.10	2.60	0.083	0.102
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060

**Ordering Information**

Device	Package	Shipping
10BQ100	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**

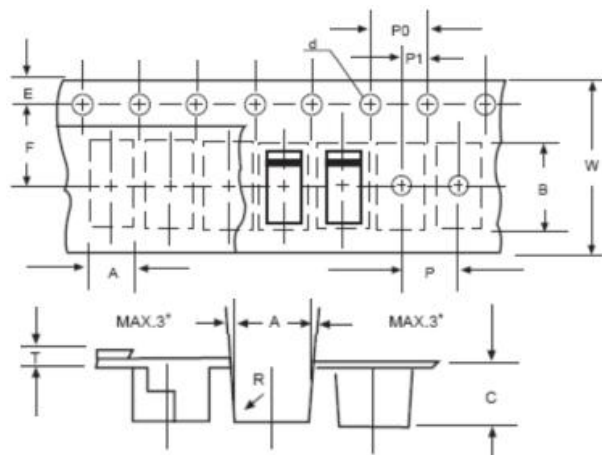


Where XXXXX is YYWWL

SB1J = Part Name  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Carrier Tape Specification SMB**



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

**Technical Data**  
**Data Sheet N0646, Rev. A**



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